

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY DOCKET NO.

248397US99DIV

SERIAL NO.

10/768,108

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Jamal RAMDANI, et al.

FILING DATE

February 2, 2004

GROUP

2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
AA	3,802,967	04/09/74	Ladany et al.			
AB	4,174,422	11/13/79	Matthews et al.			
AC	4,404,265	09/13/83	Manasevit			
AD	4,482,906	11/13/84	Hovel et al.			
AE	4,523,211	06/11/85	Morimoto et al.			
AF	4,661,176	04/28/87	Manasevit			
AG	4,793,872	12/27/88	Meunier et al.			
AH	4,846,926	07/11/89	Kay et al.			
AJ	4,855,249	08/08/89	Akasaki et al.			
AI	4,891,091	01/02/90	Shastri			
AK	4,912,087	03/27/90	Aslam et al.			
AL	4,928,154	05/22/90	Umeno et al.			
AM	4,963,949	10/16/90	Wanlass et al.			
AN	5,141,894	08/25/92	Bisaro et al.			
AO	5,159,413	10/27/92	Calviello et al.			
AP	5,173,474	12/22/92	Connell et al.			
AQ	5,221,367	06/22/93	Chisholm et al.			
AR	5,225,031	07/06/93	McKee et al.			
AS	5,358,925	10/25/94	Neville Connell et al.			
AT	5,393,352	02/28/95	Summerfelt			
AU	5,418,216	05/23/95	Fork			
AV	5,450,812	09/19/95	McKee et al.			
AW	5,478,653	12/26/95	Guenzer			
AX	5,482,003	01/09/96	McKee et al.			
AY	5,514,484	05/07/96	Nashimoto			
AZ	5,556,463	09/17/96	Guenzer			
BA	5,588,995	12/31/96	Sheldon			
BB	5,670,798	09/23/97	Schetzina			
BC	5,733,641	03/31/98	Fork et al.			
BD	5,735,949	04/07/98	Mantl et al.			
BE	5,741,724	04/21/98	Ramdani et al.			
BF	5,810,923	09/22/98	Yano et al.			
BG	5,830,270	11/03/98	McKee et al.			
BH	5,912,068	06/15/99	Jia			
BI	6,020,222	02/01/00	Wollesen			
BJ	6,045,626	04/04/00	Yano et al.			
BK	6,064,078	05/16/00	Northrup et al.			
BL	6,064,092	05/16/00	Park			
BM	6,096,584	08/01/00	Ellis-Monaghan et al.			
BN	6,103,008	08/15/00	McKee et al.			
BO	6,136,666	10/24/00	So			
BP	6,174,755	01/16/01	Manning			
BQ	6,180,486	01/30/01	Leobandung et al.			

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Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 248397US99DIV		SERIAL NO. 10/768,108	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal RAMDANI, et al.			
				FILING DATE February 2, 2004		GROUP 2815	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
HMS	CA	3,766,370	10/16/73	Walther			
	CB	4,006,989	02/08/77	Andringa			
	CC	4,284,329	08/18/81	Smith et al.			
	CD	4,777,613	10/11/98	Shahan et al.			
	CE	4,802,182	01/31/89	Thornton et al.			
	CF	4,882,300	11/21/89	Inoue et al.			
	CG	4,896,194	01/23/90	Suzuki			
	CH	4,999,842	03/12/91	Huang et al.			
	CI	5,081,062	01/14/92	Vasudev et al.			
	CJ	5,155,658	10/13/92	Inam et al.			
	CK	5,248,564	09/28/93	Ramesh			
	CL	5,260,394	11/09/93	Tazaki et al.			
	CM	5,270,298	12/14/93	Ramesh			
	CN	5,286,985	02/15/94	Taddiken			
	CO	5,310,707	05/10/94	Oishi et al.			
	CP	5,326,721	07/05/94	Summerfelt			
	CQ	5,404,581	04/04/95	Honjo			
	CR	5,418,389	05/23/95	Watanabe			
	CS	5,436,759	07/25/95	Dijail et al.			
	CT	5,576,879	11/19/96	Nashimoto			
	CU	5,606,184	02/25/97	Abrokwah, et al.			
	CV	5,640,267	06/17/97	May et al.			
	CW	5,674,366	10/07/97	Hayashi et al.			
	CX	5,729,641	03/17/98	Chandonnet et al.			
CY	5,790,583	08/04/98	Ho				
CZ	5,825,799	10/20/98	Ho et al.				
DA	5,857,049	01/05/99	Beranek et al.				
DB	5,874,860	02/23/99	Brunel et al.				
DC	5,926,496	07/20/99	Ho et al.				
DD	5,937,285	08/10/99	Abrokwah, et al.				
DE	5,981,400	11/09/99	Lo				
DF	5,990,495	11/23/99	Ohba				
DG	6,002,375	12/14/99	Corman et al.				
DH	6,008,762	12/28/99	Nghiem				
DI	6,055,179	04/25/00	Koganei et al.				
DJ	6,107,653	08/22/00	Fitzgerald				
DK	6,113,690	09/05/00	Yu et al.				
DL	6,114,996	09/05/00	Nghiem				
DM	6,121,642	09/19/00	Newns				
DN	6,128,178	10/03/00	Newns				
DO	6,143,072	11/07/00	McKee et al.				
DP	6,184,144	02/06/01	Lo				
DQ	6,222,654	04/24/01	Fligo				

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
B/M	EA	4,484,332	11/20/84	Hawrylo			
	EB	4,815,084	03/21/89	Scifres et al.			
	EC	4,876,219	10/24/89	Eshita et al.			
	ED	4,963,508	10/16/90	Umeno et al.			
	EE	5,060,031	10/22/91	Abrokwah, et al.			
	EF	5,063,166	11/05/91	Mooney et al.			
	EG	5,116,461	05/26/92	Lebby et al.			
	EH	5,127,067	06/30/92	Delcoco et al.			
	EI	5,144,409	09/01/92	Ma			
	EJ	5,293,050	03/08/94	Chapple-Sokol et al			
	EK	5,356,831	10/18/94	Calviello et al.			
	EL	5,391,515	02/21/95	Kao et al.			
	EM	5,442,191	08/15/95	Ma			
	EN	5,444,016	08/22/95	Abrokwah, et al.			
	EO	5,480,829	01/02/96	Abrokwah, et al.			
	EP	5,528,414	06/18/96	Oakley			
	EQ	5,614,739	03/25/97	Abrokwah et al.			
	ER	5,729,394	03/17/98	Sevier et al.			
	ES	5,731,220	03/24/98	Tsu et al.			
	ET	5,764,676	06/09/98	Paoli et al.			
	EU	5,777,762	07/07/98	Yamamoto			
	EV	5,778,018	07/07/98	Yoshikawa et al.			
	EW	5,778,116	07/07/98	Tomich			
	EX	5,801,105	09/01/98	Yano et al.			
	EY	5,828,080	10/27/98	Yano et al.			
	EZ	5,858,814	01/12/99	Goossen et al.			
	FA	5,861,966	01/19/99	Ortel			
	FB	5,883,996	03/16/99	Knapp et al.			
	FC	5,995,359	11/30/99	Klee et al.			
	FD	6,058,131	05/02/00	Pan			
FE	6,137,603	10/24/00	Henmi				
FF	6,146,906	11/14/00	Inoue et al.				
FG	6,173,474	01/16/01	Conrad				
FH	6,180,252	01/30/01	Farrell et al.				
FI	4,242,595	12/30/0	Lehovec				
FJ	4,398,342	08/16/83	Pitt et al.				
FK	4,424,589	01/03/84	Thomas et al.				
FL	4,876,208	10/24/89	Gustafson et al.				
FM	4,482,422	11/84	McGinn et al.				
FN	4,667,088	05/19/87	Kramer				
FO	4,772,929	09/20/88	Manchester et al.				
FP	4,841,775	06/27/89	Ikeda et al.				
FQ	4,845,044	07/04/88	Ariyoshi et al.				

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LIST OF REFERENCES CITED BY APPLICANT.				APPLICANT Jamal RAMDANI, et al.			
				FILING DATE February 2, 2004		GROUP 2815	
U.S. PATENT DOCUMENTS							
EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
MB	GA	4,868,376	09/19/89	Lessin et al.			
	GB	4,885,376	12/05/89	Verkade			
	GC	4,888,202	12/89	Murakami et al.			
	GD	4,891,091	12/90	Wanlass et al.			
	GE	5,051,790	09/24/91	Hammer			
	GF	5,055,445	10/08/91	Belt et al.			
	GG	5,081,519	11/14/92	Nishimura et al.			
	GH	5,143,854	09/01/92	Pirung et al.			
	GI	5,185,589	02/09/93	Krishnaswamy et al.			
	GJ	5,191,625	03/02/93	Gustavsson			
	GK	5,194,397	03/16/93	Cook et al.			
	GL	5,208,182	05/04/93	Narayan et al.			
	GM	5,216,729	06/01/93	Berger et al.			
	GN	5,314,547	05/24/94	Heremans et al.			
	GO	5,352,926	10/04/94	Andrews			
	GP	5,356,509	10/18/94	Terranova et al.			
	GQ	5,371,734	12/06/94	Fischer			
	GR	5,372,992	12/94	Itozaki et al.			
	GS	5,405,802	04/11/95	Yamagata et al.			
	GT	5,442,561	08/15/95	Yoshizawa et al.			
	GU	5,453,727	09/26/95	Shibasaki et al.			
	GV	5,466,631	11/14/95	Ichikawa et al.			
	GW	5,473,047	12/05/95	Shi			
	GX	5,473,171	12/95	Summerfelt			
	GY	5,479,033	12/26/95	Baca et al.			
	GZ	5,486,406	01/23/96	Shi			
	HA	5,491,461	02/13/96	Partin et al.			
	HB	5,492,859	02/20/96	Sakaguchi et al.			
	HC	5,494,711	02/27/96	Takeda et al.			
	HD	5,504,035	04/02/96	Rostoker et al.			
HE	5,504,183	04/02/96	Shi				
HF	5,511,238	04/23/96	Bayraktaroglu				
HG	5,512,773	04/96	Wolf et al.				
HH	5,515,047	05/07/96	Yamakido et al.				
HI	5,515,810	05/14/96	Yamashita et al.				
HJ	5,519,235	05/96	Ramesh				
HK	5,549,977	08/96	Jin et al.				
HL	5,551,238	09/03/96	Prueitt				
HM	5,552,547	09/03/96	Shi				
HN	5,589,284	12/31/96	Summerfelt et al.				
HO	5,602,418	02/11/97	Imai et al.				
HP	5,633,724	05/27/97	King et al.				

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BMB	IA	5,650,646	07/22/97	Summerfelt			
	IB	5,656,382	08/12/97	Nashimoto			
	IC	5,659,180	08/19/97	Shen et al.			
	ID	5,661,112	08/26/97	Hatta et al.			
	IE	5,679,965	11/95	Schetzina			
	IF	5,725,641	03/10/98	MacLeod			
	IG	5,745,631	04/28/98	Reinker			
	IH	5,776,621	07/07/98	Nashimoto			
	II	5,777,350	07/07/98	Nakamura et al.			
	IJ	5,789,845	08/04/98	Wadaka et al.			
	IK	5,792,569	08/11/98	Sun et al.			
	IL	5,792,679	08/11/98	Nakato			
	IM	5,796,648	08/18/98	Kawakubo et al.			
	IN	5,801,072	09/01/98	Barber			
	IO	5,812,272	09/22/98	King et al.			
	IP	5,814,583	09/98	Itozaki et al.			
	IQ	5,825,055	10/20/98	Summerfelt			
	IR	5,827,755	10/27/98	Yonchara et al.			
	IS	5,833,603	11/10/98	Kovacs et al.			
	IT	5,838,035	11/17/98	Ramesh			
IU	5,844,260	12/01/98	Ohori				
IV	5,846,846	12/08/98	Suh et al.				
IW	5,863,326	01/26/99	Nause et al.				
IX	5,872,493	02/16/99	Ella				
IY	5,879,956	03/99	Seon et al.				
IZ	5,880,452	03/09/99	Plesko				
JA	5,883,564	03/16/99	Partin				
JB	5,907,792	05/25/99	Droopad et al.				
JC	5,937,274	08/10/99	Kondow et al.				
JD	5,948,161	09/07/99	Kizuki				
JE	5,959,879	09/28/99	Koo				
JF	5,966,323	10/99	Chen et al.				
JG	5,987,011	11/16/99	Toh				
JH	6,022,140	02/08/00	Fraden et al.				
JI	6,022,410	02/08/00	Yu et al.				
JJ	6,023,082	02/08/00	McKee et al.				
JK	6,028,853	02/22/00	Haartsen				
JL	6,049,702	04/11/00	Tham et al.				
JM	6,078,717	06/20/00	Nashimoto et al				
JN	6,088,216	07/00	Laibowitz et al.				
JO	6,090,659	07/00	Laibowitz et al.				
JP	6,107,721	08/22/00	Lakin				
JQ	6,153,010	11/28/00	Kiyoku et al				

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U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
B/M	KA	6,153,454	11/28/00	Krivokapic			
	KB	6,191,011	02/01	Gilboa et al			
	KC	6,204,737	03/20/01	Ella			
	KD	6,224,669	05/01/01	Yi et al.			
	KE	6,225,051	05/01/01	Sugiyama et al.			
	KF	6,241,821	06/05/01	Yu et al.			
	KG	6,265,749	07/24/01	Gardner et al.			
	KH	6,313,486	11/01	Kencke et al.			
	KI	6,316,832	11/13/01	Tsuzuki et al.			
	KJ	2002/0008234	01/02	Emrick			
	KK	3,670,213	06/13/72	Nakawaga et al.			
	KL	4,756,007	07/05/88	Qureshi et al.			
	KM	4,773,063	09/20/88	Hunsperger et al.			
	KN	5,394,489	02/28/95	Koch			
	KO	5,406,202	04/11/95	Mehrgardt et al.			
	KP	5,528,067	06/18/96	Farb et al.			
	KQ	5,572,052	11/05/96	Kashihara et al.			
	KR	5,767,543	06/16/98	Ooms et al.			
	KS	6,175,497	01/16/01	Tseng et al.			
	KT	6,197,503	03/06/01	Vo-Dinh et al.			
KU	6,248,459	06/19/01	Wang et al.				
KV	6,252,261	06/26/01	Usui et al.				
KW	6,255,198	07/03/01	Linthicum et al.				
KX	6,268,269	07/31/01	Lee et al.				
KY	6,291,319	09/18/01	Yu et al.				
KZ	6,316,785	11/13/01	Nunoue et al.				
LA	6,343,171	01/29/02	Yoshimura et al.				
LB	4,965,649	10/23/90	Zanio et al.				
LC	6,253,649	05/01	Kawahara et al.				
LD	6,211,096	04/01	Allman et al.				
LE	6,239,449	05/29/01	Fafard et al.				
LF	2001/0013313	08/16/01	Droopad et al.				
LG	6,184,044	02/06/01	Sone et al.				
LH	6,011,646	01/04/00	Mirkarimi et al.				
LI	5,227,196	07/13/93	Itoh				
LJ	6,150,239	11/21/00	Goesele et al.				
LK	5,441,577	08/15/95	Sasaki et al.				
LL	4,459,325	07/10/84	Nozawa et al.				
LM	4,392,297	07/12/83	Little				
LN	4,289,920	09/15/81	Hovel				
LO	5,281,834	01/25/94	Cambou et al.				
LP	4,901,133	02/13/90	Curran et al.				
LQ	5,514,904	05/07/96	Onga et al.				

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EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BMB	MA	5,553,089	09/03/96	Seki et al.			
	MB	5,528,057	06/18/96	Yanagase et al.			
	MC	6,229,159	05/08/01	Suzuki			
	MD	4,748,485	05/31/88	Vasudev			
	ME	4,984,043	01/08/91	Vinal			
	MF	5,754,319	05/19/98	Van De Voorde et al.			
	MG	6,108,125	08/22/00	Yano			
	MH	5,073,981	12/17/91	Giles et al.			
	MI	5,140,651	08/18/92	Soref et al.			
	MJ	5,610,744	03/11/97	Ho et al.			
	MK	6,362,017	03/26/02	Manabe et al.			
	ML	6,242,686	06/05/01	Kishimoto et al.			
	MM	5,689,123	11/18/97	Major et al.			
	MN	5,670,800	09/23/97	Nakao et al.			
	MO	5,067,809	11/26/91	Tsubota			
	MP	5,596,205	01/21/97	Reedy et al.			
	MQ	6,175,555	01/16/01	Hoole			
	MR	5,357,122	10/18/94	Okubora et al.			
	MS	4,084,130	04/11/78	Holton			
	MT	6,093,302	07/25/00	Montgomery			
MU	6,372,813	04/16/02	Johnson et al.				
MV	5,608,046	03/04/97	Cook et al.				
MW	5,955,591	09/21/99	Imbach et al.				
MX	6,022,963	02/08/00	McGall et al.				
MY	6,083,697	07/04/00	Beecher et al.				
MZ	5,063,081	11/05/91	Cozzette et al.				
NA	5,479,317	12/26/95	Ramesh				
NB	5,306,649	04/26/94	Hebert				
NC	5,962,069	10/05/99	Schindler et al.				
ND	5,541,422	07/30/96	Wolf et al.				
NE	5,873,977	02/23/99	Desu et al.				
NF	5,538,941	07/23/96	Findikoglu et al.				
NG	6,046,464	04/04/00	Schetzina				
NH	6,235,145	05/22/01	Li et al.				
NI	5,610,744	03/11/97	Ho et al.				
NJ	5,280,013	01/18/94	Newman et al.				
NK	6,348,373 B1	02/19/02	Ma et al.				
NL	6,339,664 B1	01/15/02	Farjady et al.				
NM	4,439,014	03/27/84	Stacy et al.				
NN	4,889,402	12/26/89	Reinhart				
NO	5,963,291	10/05/99	Wu et al.				
NP	6,011,641	01/04/00	Shin et al.				
NQ	6,340,788 B1	01/22/02	King et al.				

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LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Jamal RAMDANI, et al.			
				FILING DATE February 2, 2004		GROUP 2815	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
BWB	OA	5,807,440	09/15/98	Kubota et al.			
	OB	4,681,982	07/21/87	Yoshida			
	OC	4,629,821	12/16/86	Bronstein-Bonte et al.			
	OD	4,452,720	06/05/84	Harada et al.			
	OE	3,935,031	01/27/76	Adler			
	OF	5,760,426	06/02/98	Marx et al.			
	OG	5,053,835	10/01/91	Horikawa et al.			
	OH	6,326,645 B1	12/04/01	Kadota			
	OI	5,770,887	06/23/98	Tadatomo et al.			
	OJ	6,372,356 B1	04/16/02	Thornton et al.			
	OK	4,774,205	09/27/88	Choi et al.			
	OL	6,359,330 B1	03/19/02	Goudard			
	OM	5,312,765	05/17/94	Kanber			
	ON	5,734,672	03/31/98	McMinn et al.			
	OO	6,367,699 B2	04/09/02	Ackley			
	OP	5,530,235	06/25/96	Stefik et al.			
	OQ	5,623,552	04/22/97	Lane			
	OR	5,481,102	01/02/96	Hazelrigg, Jr.			
	OS	6,134,114	10/17/00	Ungermann et al.			
	OT	5,984,190	11/16/99	Nevill			
	OU	5,789,733	08/04/98	Jachimowicz et al.			
	OV	5,753,300	05/19/98	Wessels et al.			
	OW	6,208,453	03/27/01	Wessels et al.			
	OX	5,886,867	03/23/99	Chivukula et al.			
	OY	5,028,976	07/02/91	Ozaki et al.			
	OZ	5,869,845	02/09/99	Vander Wagt et al.			
	PA	5,596,214	01/21/97	Endo			
	PB	6,391,674 B2	05/21/02	Ziegler			
	PC	6,275,122 B1	08/14/01	Speidell et al.			
	PD	6,238,946 B1	05/29/01	Ziegler			
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	PF	6,392,257	05/21/02	Ramdani et al.			
	PG	4,442,590	04/17/84	Stockton et al.			
	PH	5,603,764	02/18/97	Matsuda et al.			
	PI	6,087,681	06/11/00	Shakuda			
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	PK	6,427,066	07/30/02	Grube			
	PL	2002/0072245	06/13/02	Ooms et al.			
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	QH	5,619,051	04/08/97	Endo			
	QI	5,420,102	05/30/95	Harshavardhan et al.			
	QJ	5,210,763	05/11/93	Lewis et al.			
	QK	5,103,494	04/07/92	Mozer			
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	QP	5,484,664	01/16/96	Kitahara et al.			
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	SD	5,452,118	09/19/95	Maruska			
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	TI	6,411,756 B2	06/25/02	Sadot et al.			
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	UB	5,427,988	06/27/95	Sengupta et al.			
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	UD	5,682,046	10/28/97	Takahashi et al.			
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	UF	6,051,858	04/18/00	Uchida et al.			
	UG	6,013,553	01/11/00	Wallace et al.			
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	UI	2002/0047123 A1	04/25/02	Ramdani et al.			
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	UP	5,623,439	04/22/97	Gotoh et al.			
	UQ	4,981,714	01/01/91	Ohno et al.			
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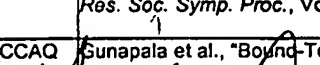
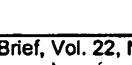
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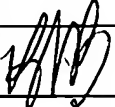
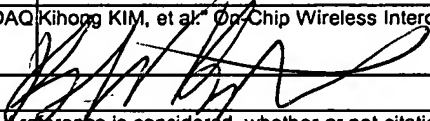
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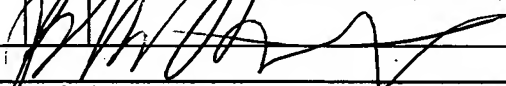
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ZMB	CCAA	Nakagawara et al., "Effects of Buffer Layers in Epitaxial Growth of SrTiO ₃ Thin Film on Si(100), <i>J. Appl. Phys.</i> , 78 (12), December 15, 1995, pp. 7226-7230.	
1	CCAB	Suzuki et al., "A Proposal of Epitaxial Oxide Thin Film Structures For Future Oxide Electronics," <i>Materials Science and Engineering B41</i> , (1996), pp. 166-173.	
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	CCAD	Wang et al., "Processing and Performance of Piezoelectric Films", Univ. Of MD, Wilcoxon Research Col, and Motorola Labs, May 11, 2000.	
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	CCAG	M. Rotter et al., "Single Chip Fused Hybrids for Acousto-Electric and Acousto-Optic Applications," <i>1997 Applied Physics Letters</i> , Vol. 70(16), April 21, 1997, pp. 2097-2099.	
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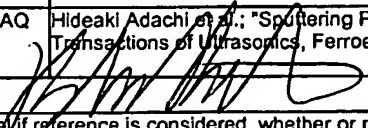
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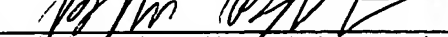
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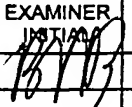
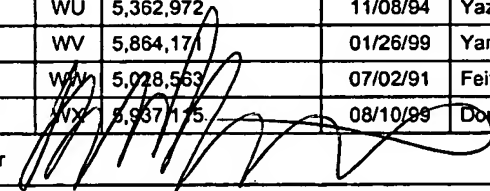
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	IIAP	M. Schreiter, et al.; "Sputtering of Self-Polarized PZT Films for IR-Detector Arrays"; 1998 IEEE; pp. 181-185					
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	JJAB	P.A. Langjahr et al.; "Epitaxial Growth and Structure of Cubic and Pseudocubic Perovskite Films on Perovskite Substrates"; Mat. Res. Soc. Symp. Proc., Vol. 401; 1995 Materials Research Society; pp. 109-114	
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	JJAD	Ben G. Streetman; "Solid State Electronic Devices"; 1990, Prentice Hall; Third Edition; pp. 320-322	
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	JJAQ	S.K. Tewksbury et al.; "Cointegration of Optoelectronics and Submicron CMOS"; Wafer Scale Integration; 1993; Proceedings, Fifth Annual IEEE; 20 January 1993; pp. 358-367	
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	KKAC	Alex Chediak et al; "Integration of GaAs/Si with Buffer Layers and Its Impact on Device Integration"; TICS 4, Prof. Sands, MSE 225, April 12, 2002; pp. 1-5	
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	KKAM	Yuji Matsumoto et al.; "Room-Temperature Ferromagnetism in Transparent Transition Metal-Doped Titanium Dioxide"; Science; 2 February 2001; Vol. 291; pp. 854-856	
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	KKAQ		
	KKAP		
	KKAQ		
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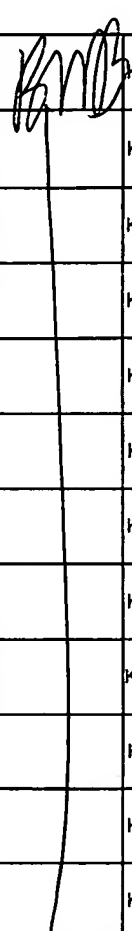
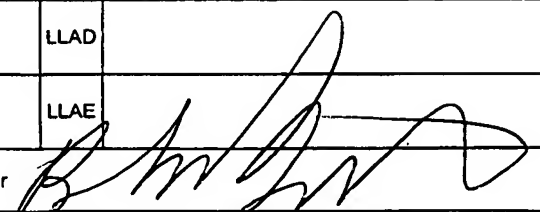
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	UT	5,528,209	06/18/96	Macdonald et al.			
	UV	5,998,781	12/07/99	Vawter et al.			
	UW	6,110,813	08/29/00	Ota et al.			
	UX	6,452,232 B1	09/17/02	Adan			
	UY	6,049,110	04/11/00	Koh			
	UZ	5,559,368	09/24/96	Hu et al.			
	VA	6,392,253 B1	05/21/02	Saxena			
	VB	5,585,288	12/17/96	Davis et al.			
	VC	5,268,327	12/07/93	Vernon			
	VD	6,198,119 B1	03/06/01	Nabatame et al.			
	VE	6,113,225	09/05/00	Miyata et al.			
	VF	5,262,659	11/16/93	Grudkowski et al.			
	VG	6,239,012 B1	05/29/01	Kinsman			
	VH	6,297,598	10/02/01	Wang et al.			
	VI	2002/140012	10/03/02	Droopad			
	VJ	4,866,489	09/12/89	Yokogawa et al.			
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	VN	4,695,120	09/22/87	Holder			
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VP	5,574,589	11/12/96	Feuer et al.				
VQ	5,510,665	04/23/96	Conley				
VR	4,804,866	02/14/89	Akiyama				
VS	5,057,694	10/15/91	Idaka et al.				
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VU	5,719,417	02/17/98	Roeder et al.				
VW	5,998,818	12/07/99	Yokoyama et al.				
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	VW	2002/0079576	06/27/02	Seshan			
	VX	5,148,504	09/15/92	Levi et al.			
	VY	2002/0195610 A1	12/26/02	Klosowiak			
	VZ	5,477,363	12/19/95	Matsuda			
	WA	5,905,571	05/18/99	Butler et al.			
	WB	5,570,226	10/29/96	Ota			
	WC	5,087,829	02/11/92	Ishibashi et al.			
	WD	2001/0020278 A1	09/06/01	Salto			
	WE	6,496,469 B1	12/17/02	Uchizaki			
	WF	5,679,947	10/21/97	Doi et al.			
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	WK	6,376,337 B1	04/23/02	Wang et al.			
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	WM	5,216,359	06/01/93	Makki et al.			
	WN	6,307,996 B1	10/23/01	Nashimoto et al.			
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	WZ	4,801,184	01/31/89	Revelli			
	XA	5,140,387	08/18/92	Okazaki et al.			
	XB	5,410,622	04/25/95	Okada et al.			
	XC	6,064,783	05/16/00	Congdon et al.			
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	CBC	EP 1 035 759	09/13/00	Europe			
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	CBE	5-232307	09/10/93	JAPAN W/ENGLISH ABSTRACT			
	CBF	5-243525	09/31/93	JAPAN W/ENGLISH ABSTRACT			
	CBG	3-171617	07/25/91	JAPAN W/ENGLISH ABSTRACT			
	CBH	EP 1 089 338	04/04/01	EUROPE			
	CBI	01 294594	11/28/99	JAPAN (ABSTRACT)			
	CBJ	05 221800	08/31/93	JAPAN (ABSTRACT)			
	CBK	03-149882	11/07/89	JAPAN			
	CBL	0 614 256	09/07/94	EUROPE			
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	CBO	WO 02/08806	01/31/02	WIPO			
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	CBR	0 600 658	06/08/94	EUROPE			
	CBS	0 412 002	02/06/91	EUROPE			
	CBT	2000-349278	12/15/00	JAPAN (ENGLISH ABSTRACT)			
	CBU	01-196809	08/08/89	JAPAN (ENGLISH ABSTRACT)			
	CBV	0 619 283	10/12/94	EUROPE			
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	CBY						
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	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
	XU	6,232,242 B1	05/15/01	HATA ET AL			
	XV	4,378,259	03/29/83	HASEGAWA ET AL			
	XW	6,278,541 B1	08/21/01	BAKER			
	XY	4,298,247	11/03/81	MICHELET ET AL			
	XZ	4,174,504	11/13/79	CHENAUSSKY ET AL			
	YA	3,758,199	09/11/73	THAXTER			
	YB	6,362,558 B1	03/26/02	FUKUI			
	YC	6,140,746	10/31/00	MIYASHITA ET AL			
	YD	2002/0076878 A1	06/20/02	WASA ET AL			
	YE	6,419,849 B1	07/16/02	QIU ET AL			
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	YK	6,538,359 B1	03/25/03	HIRAKU ET AL			
	YL	6,498,358 B1	12/24/02	LACH ET AL			
	YM	5,387,811	02/07/95	SAIGO			
	YN	5,523,602	06/04/96	HORIUCHI ET AL			
	YO	5,362,998	11/08/94	IWAMURA ET AL			
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	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
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	ZH	3,818,451	06/18/74	COLEMAN			
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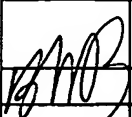
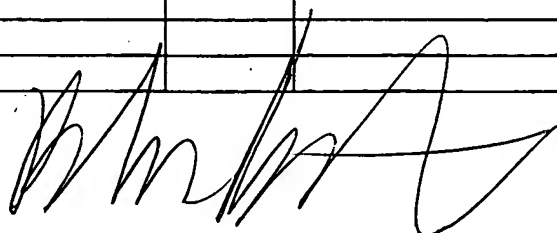
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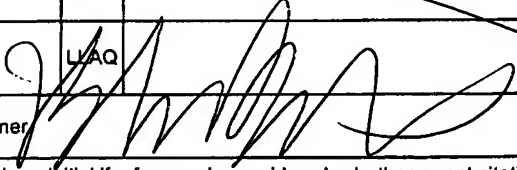
FILING DATE
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2815

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		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION	
					YES	NO
	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT		
	CCB	2 152 315	07/31/85	GREAT BRITAIN		
	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT		
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)		
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	CCF	1 043 427	10/11/00	EUROPE		
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	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT		
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	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001					
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<i>BMP</i>	CCS	WO 99/67882	12/29/99	WIPO			
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	CCX	1 069 605	01/17/01	EUROPE			
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